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BAR DIGIT LED DISPLAY

**LBD336B-XX**

**DATA SHEET**

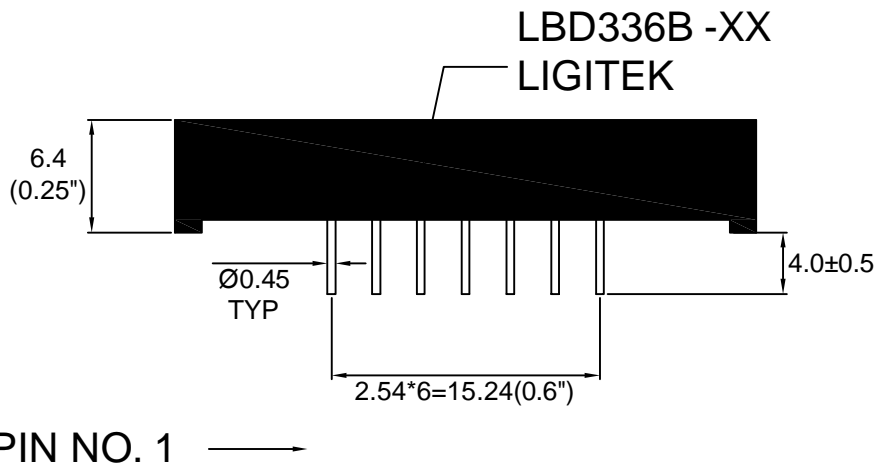
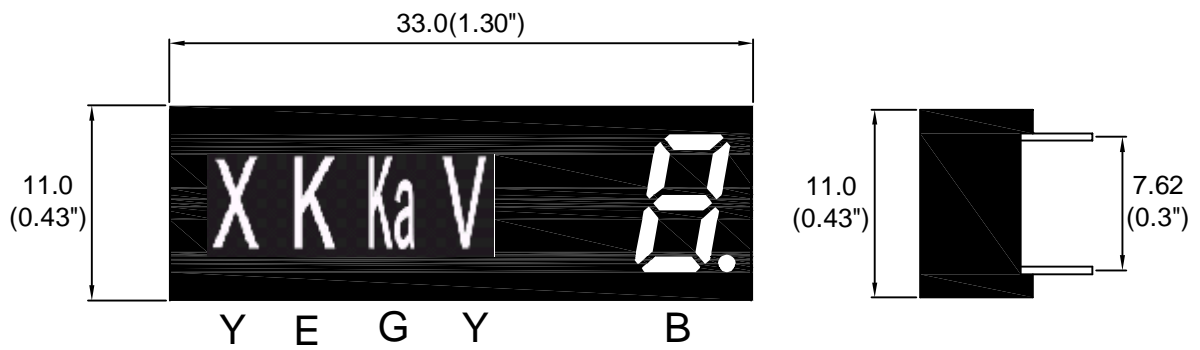
DOC. NO : QW0905-LBD336B-XX

REV. : A

DATE : 20 - Aug. - 2008



### Package Dimensions

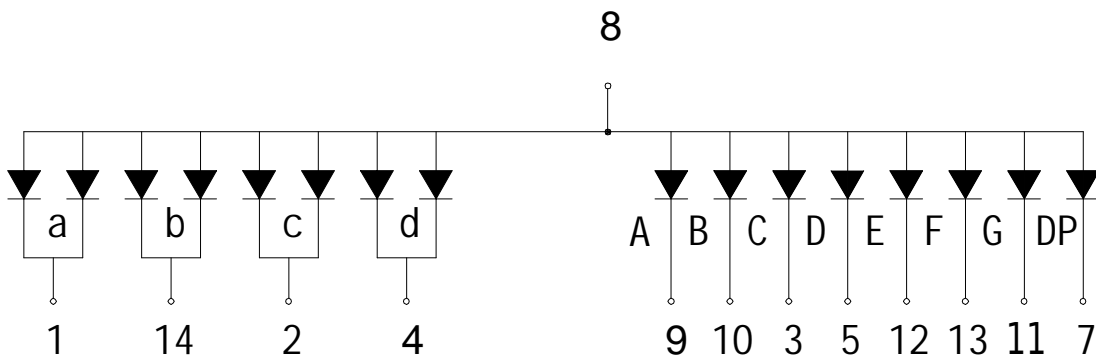


- Note : 1.All dimension are in millimeters and (Inch) tolerance is  $\pm 0.25\text{mm}(0.01\text{'})$  unless otherwise noted.  
 2.Specifications are subject to change without notice.  
 3.Film:temperature-resistant  $\leq 100^{\circ}\text{C}$ .



Internal Circuit Diagram

LBD336B-XX



**Electrical Connection**

PIN NO.	LBD336B-XX
1.	Cathode a
2.	Cathode c
3.	Cathode C
4.	Cathode d
5.	Cathode D
6.	NC
7.	Cathode DP
8.	Common Anode
9.	Cathode A
10.	Cathode B
11.	Cathode G
12.	Cathode E
13.	Cathode F
14.	Cathode b



## Absolute Maximum Ratings at Ta=25 °C

Parameter	Symbol	Ratings				UNIT
		Y	E	G	SBI	
Forward Current Per Chip	IF	20	30	30	30	mA
Peak Forward Current Per Chip (Duty 1/10,0.1ms Pulse Width)	IFP	80	120	120	70	mA
Power Dissipation Per Chip	PD	60	100	100	120	mW
Reverse Current Per Any Chip	Ir		10		50	$\mu A$
Electrostatic Discharge( * )	ESD	---			500	V
Operating Temperature	Topr	-25 ~ +85				°C
Storage Temperature	Tstg	-25 ~ +85				°C

\* Static Electricity or power surge will damage the LED. Use of a conductive wrist band or anti-electrostatic glove is recommended when handling these LED. All devices, equipment and machinery must be properly grounded.

## Part Selection And Application Information(Ratings at 25°C)

PART NO	CHIP		common cathode or anode	$\lambda P$ (nm)	$\lambda D$ (nm)	$\Delta \lambda$ (nm)	Electrical					IV-M
	Material	Emitted					Vf(v)			Iv(mcd)		
							Min.	Typ.	Max.	Min.	Typ.	
LBD336B-XX	GaAsP/GaP	Yellow	Common Anode	585	---	35	1.7	2.1	2.6	---	---	2:1
	GaAsP/GaP	Orange		635	---	45	1.7	2.1	2.6	---	---	
	GaP	Green		565	---	30	1.7	2.1	2.6	---	---	
	InGaN/SiC	Blue		430	465	65	---	3.8	4.7	3.05	5.0	

Note : 1.The forward voltage data did not including  $\pm 0.1V$  testing tolerance.

2. The luminous intensity data did not including  $\pm 15\%$  testing tolerance.

**Test Condition For Each Parameter**

Parameter	Symbol	Unit	Test Condition
Forward Voltage Per Chip	V <sub>f</sub>	volt	I <sub>f</sub> =10mA
Forward Voltage Per Chip	V <sub>f</sub>	volt	I <sub>f</sub> =20mA
Luminous Intensity Per Chip	I <sub>v</sub>	mcd	I <sub>f</sub> =10mA
Peak Wavelength	λ <sub>P</sub>	nm	I <sub>f</sub> =20mA
Dominant Wavelength	λ <sub>D</sub>	nm	I <sub>f</sub> =20mA
Spectral Line Half-Width	Δλ	nm	I <sub>f</sub> =20mA
Reverse Current Any Chip	I <sub>r</sub>	μA	V <sub>r</sub> =5V
Luminous Intensity Matching Ratio	IV-M		



### Typical Electro-Optical Characteristics Curve

Y CHIP

Fig.1 Forward current vs. Forward Voltage

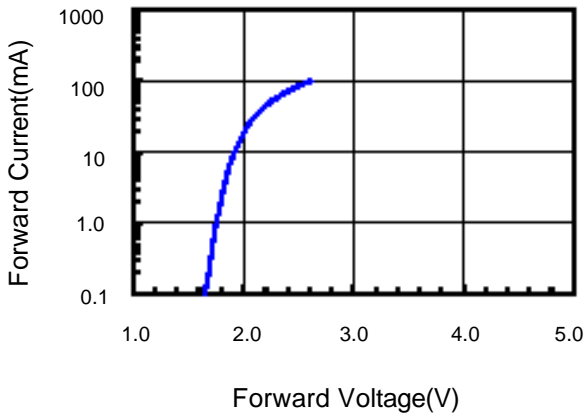


Fig.2 Relative Intensity vs. Forward Current

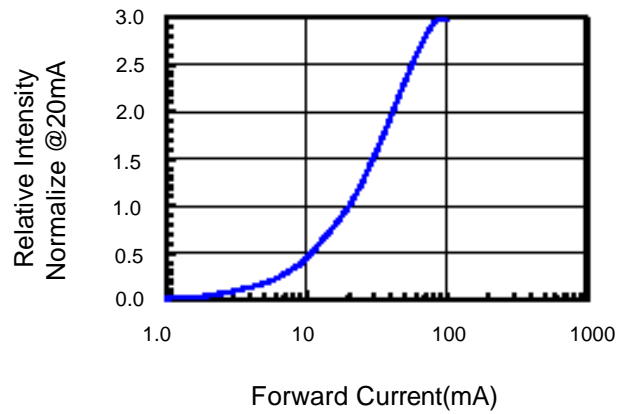


Fig.3 Forward Voltage vs. Temperature

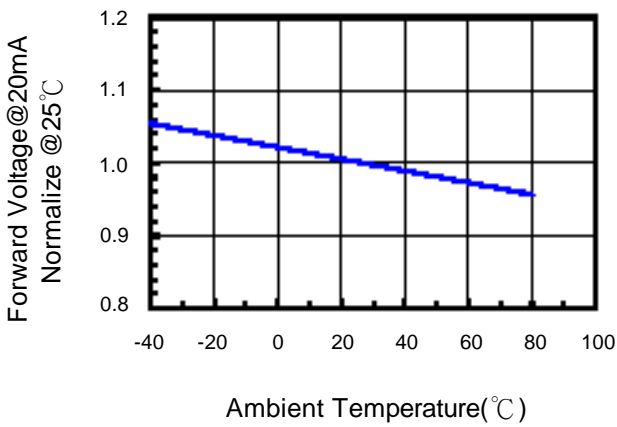


Fig.4 Relative Intensity vs. Temperature

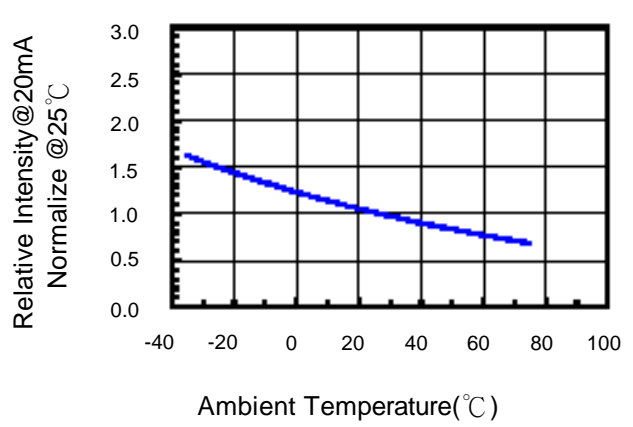
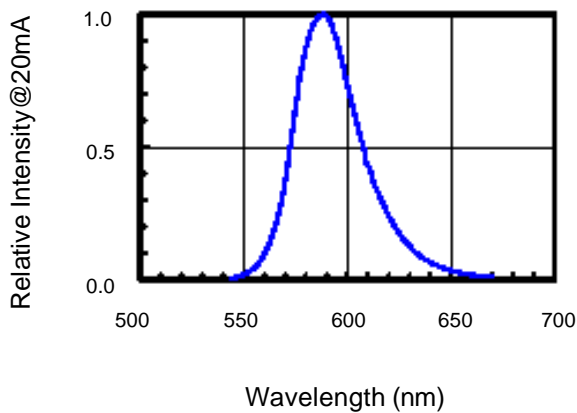


Fig.5 Relative Intensity vs. Wavelength





### Typical Electro-Optical Characteristics Curve

E CHIP

Fig.1 Forward current vs. Forward Voltage

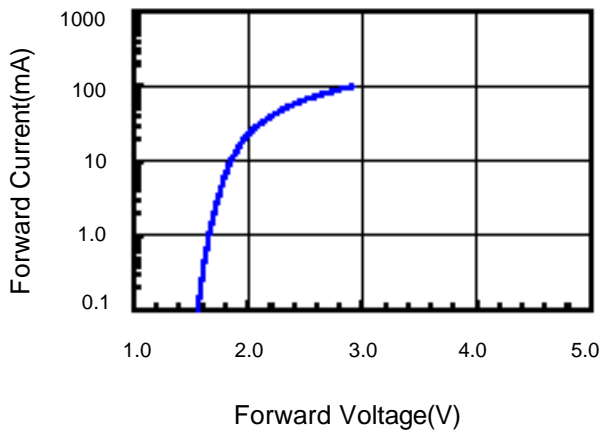


Fig.2 Relative Intensity vs. Forward Current

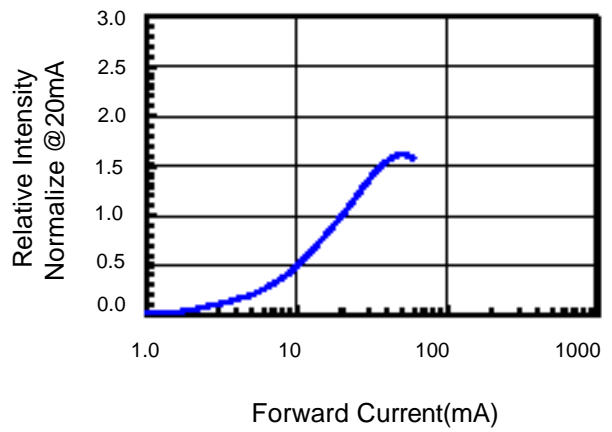


Fig.3 Forward Voltage vs. Temperature

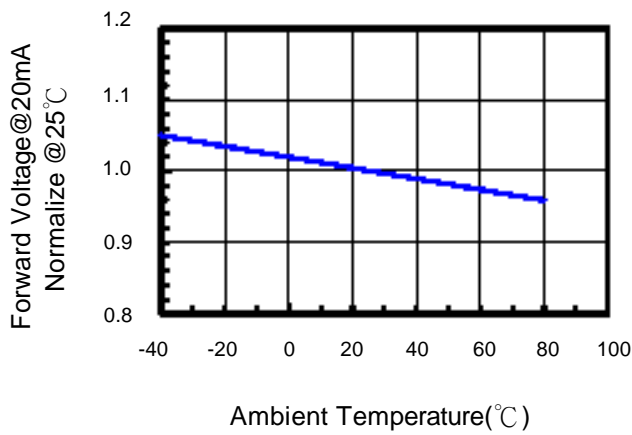


Fig.4 Relative Intensity vs. Temperature

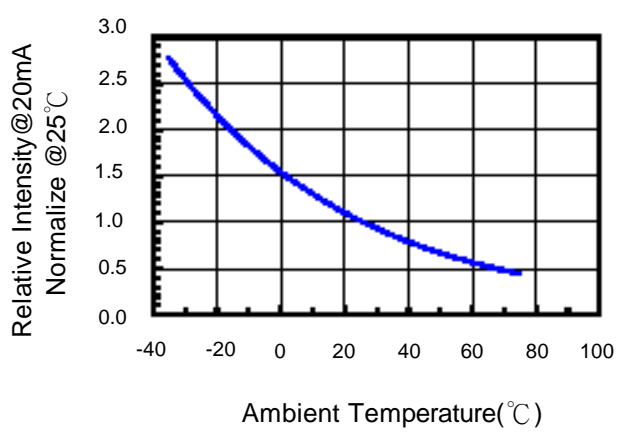
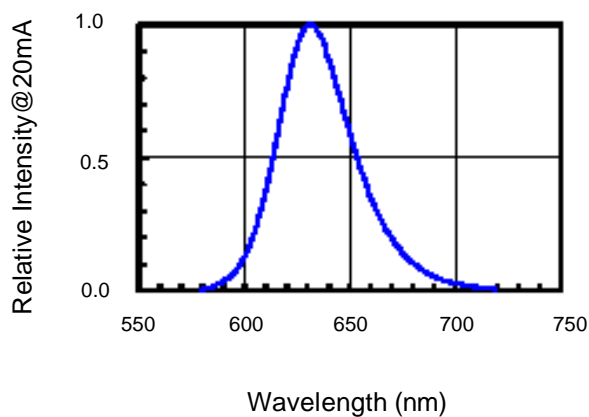


Fig.5 Relative Intensity vs. Wavelength







### Typical Electro-Optical Characteristics Curve

G CHIP

Fig.1 Forward current vs. Forward Voltage

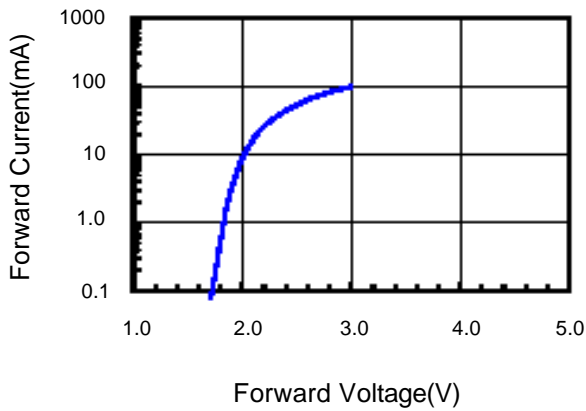


Fig.2 Relative Intensity vs. Forward Current

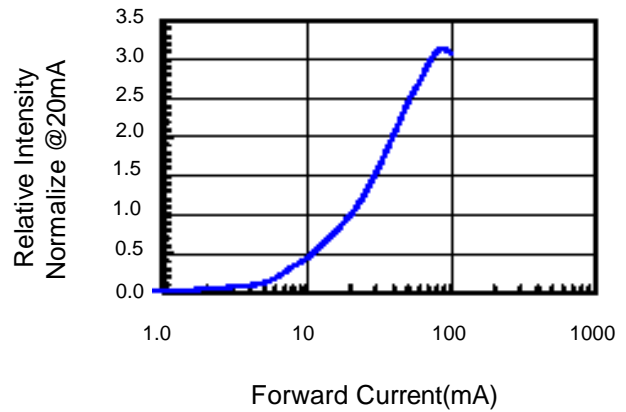


Fig.3 Forward Voltage vs. Temperature

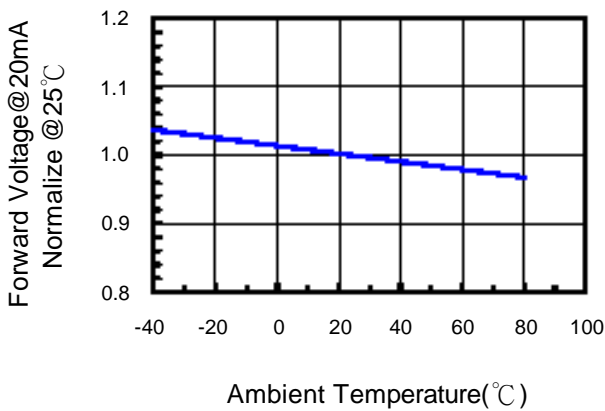


Fig.4 Relative Intensity vs. Temperature

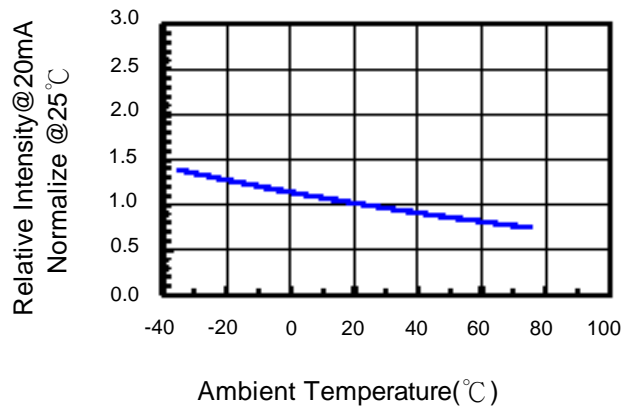
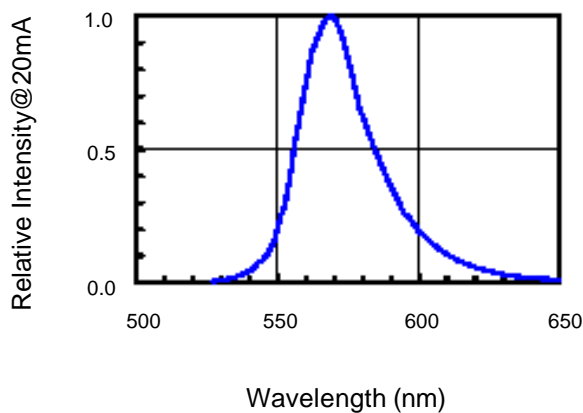


Fig.5 Relative Intensity vs. Wavelength





### Typical Electro-Optical Characteristics Curve

#### SBI CHIP

Fig.1 Forward current vs. Forward Voltage

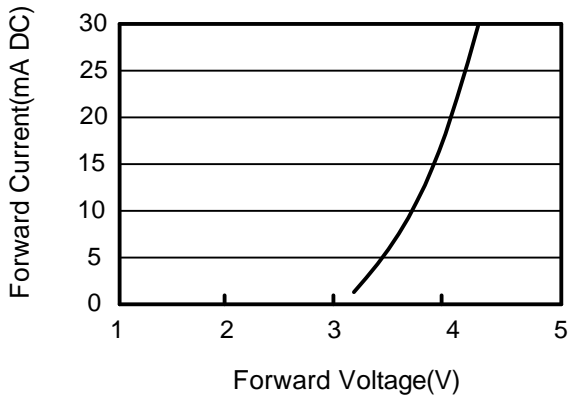


Fig.2 Relative Intensity vs. Wavelength

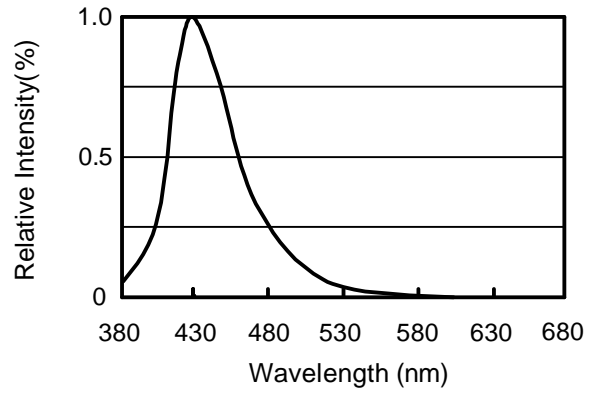


Fig.3 Relative Intensity vs. Forward Current

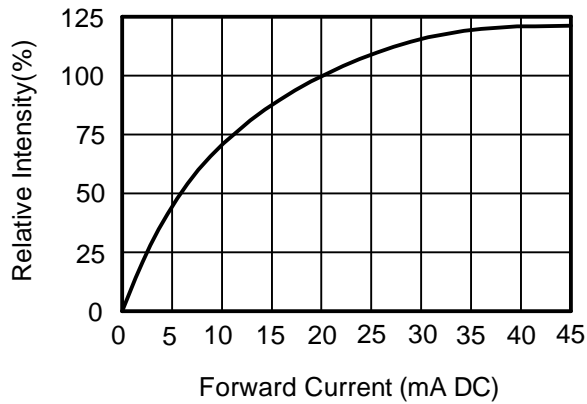


Fig.4 Relative Intensity vs. Lead Temperature

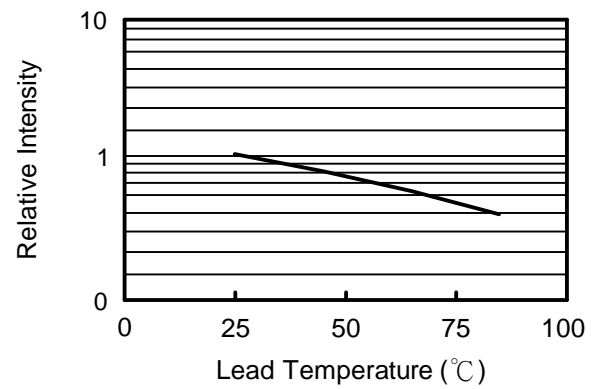
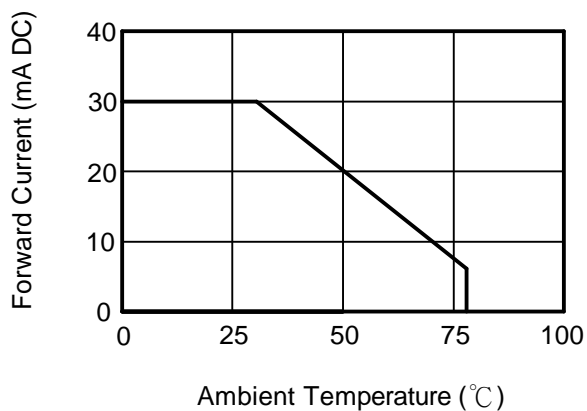


Fig.5 Forward Current vs. Ambient Temperature





Reliability Test:

Test Item	Test Condition	Description	Reference Standard
Operating Life Test	1.Under Room Temperature 2.If=10mA 3.t=1000 hrs (-24hrs, +72hrs)	This test is conducted for the purpose of determining the resistance of a part in electrical and thermal stressed.	MIL-STD-750: 1026 MIL-STD-883: 1005 JIS C 7021: B-1
High Temperature Storage Test	1.Ta=105 °C ±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of high temperature for hours.	MIL-STD-883:1008 JIS C 7021: B-10
Low Temperature Storage Test	1.Ta=-40 °C ±5°C 2.t=1000 hrs (-24hrs, +72hrs)	The purpose of this is the resistance of the device which is laid under condition of low temperature for hours.	JIS C 7021: B-12
High Temperature High Humidity Test	1.Ta=65 °C ±5°C 2.RH=90%~95% 3.t=240hrs ±2hrs	The purpose of this test is the resistance of the device under tropical for hours.	MIL-STD-202:103B JIS C 7021: B-11
Thermal Shock Test	1.Ta=105 °C ±5°C & -40 °C ±5°C (10min) (10min) 2.total 10 cycles	The purpose of this is the resistance of the device to sudden extreme changes in high and low temperature.	MIL-STD-202: 107D MIL-STD-750: 1051 MIL-STD-883: 1011
Solder Resistance Test	1.T.Sol=260 °C ±5°C 2.Dwell time= 10 ±1sec.	This test intended to determine the thermal characteristic resistance of the device to sudden exposures at extreme changes in temperature when soldering the lead wire.	MIL-STD-202: 210A MIL-STD-750: 2031 JIS C 7021: A-1
Solderability Test	1.T.Sol=230 °C ±5°C 2.Dwell time=5 ±1sec	This test intended to see soldering well performed or not.	MIL-STD-202: 208D MIL-STD-750: 2026 MIL-STD-883: 2003 JIS C 7021: A-2